

Title (en)

METHOD FOR MANUFACTURING A MONOCRYSTALLINE LAYER OF DIAMOND OR IRIIDIUM MATERIAL, AND SUBSTRATE FOR EPITAXIALLY GROWING A MONOCRYSTALLINE LAYER OF DIAMOND OR IRIIDIUM MATERIAL

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER MONOKRISTALLINEN SCHICHT AUS DIAMANT ODER IRIIDIUM UND SUBSTRAT ZUM EPITAKTISCHEN ZÜCHTEN EINER MONOKRISTALLINEN SCHICHT AUS DIAMANT ODER IRIIDIUM

Title (fr)

PROCÉDÉ DE FABRICATION D'UNE COUCHE MONOCRISTALLINE DE MATÉRIAU DIAMANT OU IRIIDIUM ET SUBSTRAT POUR CROISSANCE PAR ÉPITAXIE D'UNE COUCHE MONOCRISTALLINE DE MATÉRIAU DIAMANT OU IRIIDIUM

Publication

EP 3775329 A1 20210217 (FR)

Application

EP 19721378 A 20190326

Priority

- FR 1800255 A 20180328
- IB 2019000196 W 20190326

Abstract (en)

[origin: WO2019186262A1] Method for manufacturing a monocrystalline layer of diamond or iridium material, including transferring a monocrystalline seed layer of SrTiO₃ material onto a support substrate of silicon material, followed by epitaxially growing the monocrystalline layer of diamond or iridium material.

IPC 8 full level

C30B 23/02 (2006.01); **C30B 25/18** (2006.01); **C30B 29/02** (2006.01); **C30B 29/04** (2006.01); **H01L 21/762** (2006.01)

CPC (source: EP KR US)

C30B 23/025 (2013.01 - EP KR US); **C30B 25/183** (2013.01 - EP KR US); **C30B 29/02** (2013.01 - EP KR); **C30B 29/04** (2013.01 - EP KR US); **C30B 29/06** (2013.01 - US); **H01L 21/02293** (2013.01 - US); **H01L 21/76254** (2013.01 - EP KR)

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

WO 2019186262 A1 20191003; CN 111936676 A 20201113; EP 3775329 A1 20210217; FR 3079535 A1 20191004; FR 3079535 B1 20220318; JP 2021518322 A 20210802; JP 7408893 B2 20240109; KR 102654904 B1 20240404; KR 20200136437 A 20201207; SG 11202009528Q A 20201029; US 11935743 B2 20240319; US 2021020434 A1 20210121

DOCDB simple family (application)

IB 2019000196 W 20190326; CN 201980021528 A 20190326; EP 19721378 A 20190326; FR 1800255 A 20180328; JP 2020549793 A 20190326; KR 20207030291 A 20190326; SG 11202009528Q A 20190326; US 201917042728 A 20190326